

ABSTRACT AMENDMENTS

Replace the Abstract with:

~~The invention provides a~~ A semiconductor device having ~~stability in~~ stable device characteristics, in which variation in contact resistance between silicon and poly-silicon or between poly-silicon and poly-silicon is reduced. ~~The invention also provides a method of manufacturing the semiconductor device.~~ In ~~the~~ a cleaning process before forming an upper layer poly-silicon film ~~11, an H₂O₂~~ a treatment is conducted to form a thin uniform oxide film ~~20 of about 0.5nm to 10nm in thickness (to the extent of permitting an impurity to diffuse through the film)~~ on the surface of silicon. After forming the upper layer poly-silicon film 11, a removed portion is uniformly formed on the thin uniform oxide film by applying a short time, high temperature annealing treatment ~~by RTP (Rapid Thermal Process).~~